

WHAT IS CLAIMED IS:

1. A nonvolatile storage device comprising:
a plurality of external terminals;
a controller; and
a nonvolatile memory,
said controller controlling storage operation of
data inputted from said external terminals to a region
designated by said nonvolatile memory depending on
control information inputted from any of said plurality
of external terminals,

wherein the nonvolatile storage device includes:
a plurality of external data terminals to which a data
signal is inputted; pull-up circuit for pulling up the
external data terminals up to a power source voltage;
level detection circuit for detecting a potential of
said external data terminals; and a data transfer
circuit for selectively fetching the data signal
inputted to said plurality of external data terminals
and then transferring the data signal to an internal
circuit as data of a predetermined bus width, and

wherein said level detection circuit detects a
potential of a predetermined terminal of said plurality
of external data terminals when said control information
is inputted, and said data transfer circuit determines
said bus width depending on a combination of potentials
of the predetermined external data terminals.

2. The nonvolatile storage device according to claims

1, wherein eight terminals are provided in total as said external data terminals and the potentials of four external data terminals are detected by said level detection circuit.

3. The nonvolatile storage device according to claim 2, wherein when said level detection circuit detect that the potentials of said four external data terminals are all higher than the predetermined potential, said data transfer circuit fetches the data signal inputted to any one among said predetermined external data terminals and then transfers the data signal to the internal circuit.

4. The nonvolatile storage device according to claim 3, wherein when said level detection circuit detect that potential of first terminal of said four external data terminals is lower than the predetermined potential, said data transfer circuit fetches the data signal inputted to any one of said predetermined external data terminals at a higher rate than a rate when the potentials of said four external data terminals are all higher than the predetermined potential and then transfers the data signal to the internal circuit.

5. The nonvolatile storage device according to claim 4, wherein when said level detection circuit detect that potential of second terminal of said four external data terminals is lower than the predetermined potential, said data transfer circuit fetches the data signals

inputted to the four external data terminals other than said predetermined external data terminals and then transfers the data signals to the internal circuit.

6. The nonvolatile storage device according to claim 5, wherein when said level detection circuit detect that potential of third terminal of said four external terminals is lower than the predetermined potential, said data transfer circuit fetches the data signals inputted to all of said eight external data terminals and then transfers these data signals to the internal circuit.

7. The nonvolatile storage device according to claim 6, wherein any one of said eight external data terminals is also used as a terminal to which a control signal is inputted.

8. The nonvolatile storage device according to claim 7, wherein said pull-up circuit are also formed on a semiconductor chip where said controller is formed.

9. The nonvolatile storage device according to claim 8, further comprising a volatile memory for storing data which is fetched from said external data terminal and is then transferred by said data transfer circuit before the same data is written to said nonvolatile memory.

10. The nonvolatile storage device according to claim 9, further comprising a timing generation circuit for notifying a detection timing of said level detection circuit by detecting the input of said control signal.